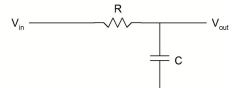


Interconnect delay

- Lumped RC model



- Charge V_{in} to V_{DD}

- The transient output voltage is

$$V_{out}(t) = V_{DD} \left(1 - e^{-\frac{t}{RC}} \right)$$

$$\frac{V_{DD}}{2} = V_{DD} \left(1 - e^{-\frac{t}{RC}} \right)$$

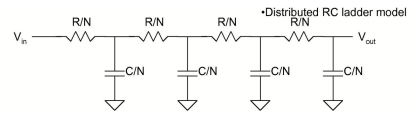
$$\frac{t_{diff}}{RC} = -\ln\left(\frac{1}{2}\right)$$

$$t_{diff} \approx .69RC$$

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Interconnect delay



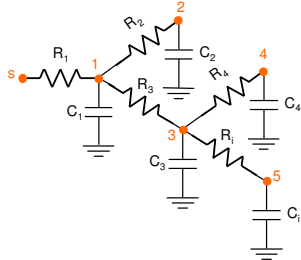
- More accurate than lumped RC model
- More difficult to solve for large N
- Need full-scale SPICE simulation

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Elmore Delay

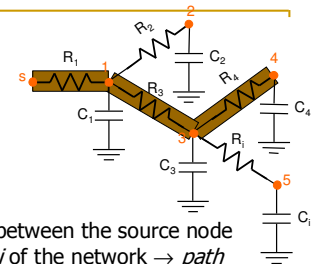
- Single line model not useful for generalized RC tree networks



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Elmore Delay



RC-tree property:

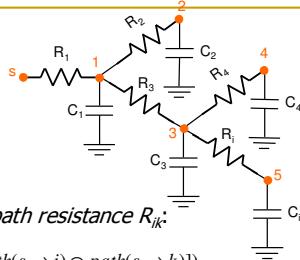
- Unique resistive path between the source node s and any other node i of the network \rightarrow path resistance R_{ij}

Example: $R_{44} = R_1 + R_3 + R_4$

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Elmore Delay



RC-tree property:

- Extended to shared path resistance R_{jk}^* :

$$R_{jk} = \sum R_j \quad \text{s.t.} \quad (R_j \in [\text{path}(s \rightarrow i) \cap \text{path}(s \rightarrow k)])$$

Example: $R_{54} = R_1 + R_3$

$R_{52} = R_1$

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Elmore Delay

- Assuming:

- Each node is initially discharged to ground
 - A step input (pulse) is applied at time $t=0$ at node s
- The Elmore delay at node i is:

$$\tau_{Di} = \sum_{k=1}^N C_k R_{ik}$$

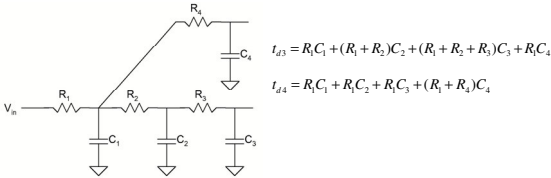
- It is an approximation: it is equivalent to first-order time constant of the network
- Proven acceptable
- Powerful mechanism for a quick estimate

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Elmore Delay

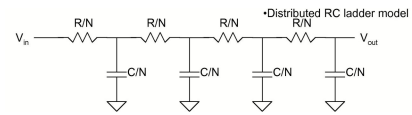
- Examples



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Elmore Delay



$$t_d = \sum_{j=1}^N \frac{C}{N} \sum_{k=1}^j \frac{R}{N}$$

$$= \frac{C}{N} \frac{R}{N} \frac{N(N+1)}{2} = RC \left(\frac{N+1}{2N} \right)$$

$$t_d = \frac{RC}{2} \text{ for } N \rightarrow \infty$$

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Interconnect Delay

- Fanout Effects

- Lines with multiple loads will have longer delays
 - Clocks
 - Data buses
 - Control lines
- Solutions
 - Wider lines for special signals
 - Buffers

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Interconnect Delay

$$t_d = \frac{RC}{2}$$

$$= \frac{1}{2} \left(r \frac{L}{w} \right) (c_a l w + 2c_p (l + w))$$

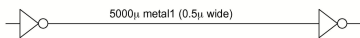
$$\approx \frac{1}{2} r c_p l^2$$

- Delay is proportional to the square of the length
- Try to avoid long lines

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Interconnect Delay



- Interconnect resistance

$$r \cdot l/w \rightarrow R = .07 \frac{5000 \mu}{0.5 \mu} = 700 \Omega$$
- Interconnect capacitance

$$C_a l w + 2C_p(l+w) \rightarrow C_{wire} = .03 \cdot 5000 \mu \cdot 0.5 \mu + .044 \cdot 2 \cdot (5000 \mu + 0.5 \mu) = 515 \text{ fF}$$
- Intrinsic load capacitance

$$C_{in} \approx 5 \text{ fF}$$
- Propagation delay

$$t_p = \frac{RC_{wire}}{2} + RC_{in} = \left(\frac{700 \cdot 515 \text{ fF}}{2} + 700 \cdot 5 \text{ fF} \right) = 184 \text{ ps}$$

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Interconnect Delay

- Avoid long interconnect delays using buffers



- Interconnect resistance

$$R = .07 \frac{2500 \mu}{0.5 \mu} = 350 \Omega$$
- Interconnect capacitance

$$C_{wire} = .03 \cdot 2500 \mu \cdot 0.5 \mu + .044 \cdot 2 \cdot (2500 \mu + 0.5 \mu) = 258 \text{ fF}$$
- Intrinsic load capacitance

$$C_{in} \approx 5 \text{ fF}$$
- Propagation delay

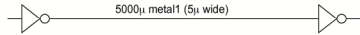
$$t_p = \frac{RC_{wire}}{2} + RC_{in} = 2 \cdot \left(\frac{350 \cdot 258 \text{ fF}}{2} + 350 \cdot 5 \text{ fF} \right) = 94 \text{ ps}$$

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Interconnect Delay

- Avoid long interconnect delays using wider lines



- Interconnect resistance

$$R = .07 \frac{5000 \mu}{5 \mu} = 70 \Omega$$

- Interconnect capacitance

$$C_{wire} = .03 \cdot 5000 \mu \cdot 5 \mu + .044 \cdot 2 \cdot (5000 \mu + 5 \mu) = 1190 \text{ fF}$$

- Intrinsic load capacitance

$$C_{in} \approx 5 \text{ fF}$$

- Propagation delay

$$t_p = \frac{RC_{wire}}{2} + RC_{in} = \left(\frac{70 \cdot 1190 \text{ fF}}{2} + 70 \cdot 5 \text{ fF} \right) = 42 \text{ ps}$$

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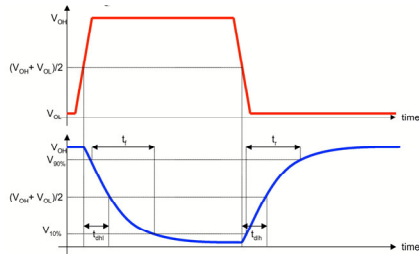
Switching Delay

- The intrinsic delay of a gate
- Transistor sizing can affect the delay
- Extrinsic capacitances can affect the delay

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Delay Definitions

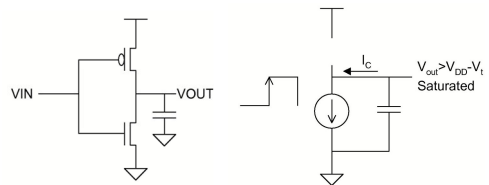


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Switching Delay

- Fall time analysis



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Fall time analysis

- Saturation Mode

$$I_c = I_{DS}$$

$$-C_L \frac{dV_{out}}{dt} = k_n \frac{(V_{DD} - V_m)^2}{2}$$

$$dt = -2 \frac{C_L}{k_n (V_{DD} - V_m)^2} dV_{out}$$

$$t_{f1} = 2 \frac{C_L}{k_n (V_{DD} - V_m)^2} \int_{V_{out}}^{V_{DD} - V_m} dV_{out}$$

$$t_{f1} = 2 \frac{C_L (V_m - V_{DD})}{k_n (V_{DD} - V_m)^2}$$

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Fall time analysis

- Linear Mode

$$I_c = I_{DS}$$

$$-C_L \frac{dV_{out}}{dt} = k_n \left[(V_{DD} - V_m) V_{out} - \frac{V_{out}^2}{2} \right]$$

$$dt = \frac{-2C_L}{k_n (2(V_{DD} - V_m)V_{out} - V_{out}^2)} dV_{out}$$

$$t_{f2} = \frac{-2C_L}{k_n} \int_{V_{out}}^{V_{DD} - V_m} \frac{dV_{out}}{(2V_{out}(V_{DD} - V_m) - V_{out}^2)}$$

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Fall time analysis

- Linear Mode

$$t_{f2} = \frac{C_L}{k_n(V_{DD} - V_m)} \ln \left(\frac{V_{out}}{2(V_{DD} - V_m) - V_{out}} \right) \Bigg|_{V_{DD}}^{V_{DD} - V_m}$$

$$= \frac{C_L}{k_n(V_{DD} - V_m)} \ln \left(\frac{19V_{DD} - 20V_m}{V_{DD}} \right)$$

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Fall time analysis

$$t_f = t_{f1} + t_{f2}$$

$$= \frac{C_L}{k_n(V_{DD} - V_m)} \left(\frac{2(V_m - 1V_{DD})}{V_{DD} - V_m} + \ln \left(\frac{19V_{DD} - 20V_m}{V_{DD}} \right) \right)$$

$$= \frac{C_L}{k_n(V_{DD} - V_m)} \left(\frac{2(n-1)}{1-n} + \ln(19-20n) \right) \quad n = \frac{V_m}{V_{DD}}$$

$$K = \frac{1}{(1-n)} \left(\frac{2(n-1)}{1-n} + \ln(19-20n) \right)$$

$$t_f = K \frac{C_L}{k_n V_{DD}}$$

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Fall time analysis

- Fall time is proportional to load capacitance and inversely proportional to V_{DD} and k_n
- Decreasing the supply voltage will increase the fall time
- Increasing the transistor width will increase k_n which will reduce the fall time
- Changing these three parameters can cause conflicting goals

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Rise time analysis

$$t_r = \frac{C_L}{k_p V_{DD} (1-p)} \left(\frac{2(p-1)}{1-p} + \ln(19-20p) \right)$$

$$K_p = \frac{1}{(1-p)} \left(\frac{2(p-1)}{1-p} + \ln(19-20p) \right) \quad p = \frac{-V_m}{V_{DD}}$$

$$t_r = K_p \frac{C_L}{k_p V_{DD}}$$

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Rise time analysis

- For equal fall times and rise times

$$t_f = t_r$$

$$K_n \frac{C_L}{k_n V_{DD}} = K_p \frac{C_L}{k_p V_{DD}}$$

$$V_m = V_{op} \rightarrow K_n = K_p$$

$$\mu_n C_{ox} \left(\frac{W_n}{L} \right) = \mu_p C_{ox} \left(\frac{W_p}{L} \right)$$

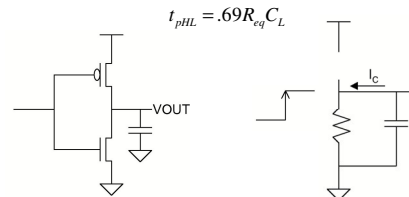
$$\frac{W_n}{W_p} = \frac{\mu_n}{\mu_p} \approx 2-3$$

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Propagation Delay

- As with interconnect delay, find the equivalent resistance and load capacitance of the transistor



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Propagation Delay

$$R_{eq} = \text{avg}(R_{on}(t)) = \frac{1}{t_2 - t_1} \int_{t_1}^{t_2} \frac{V_{DS}(t)}{I_{DS}(t)} dt$$

- Propagation delay is the time for voltage to reach half way point - so integrate from V_{DD} to $V_{DD}/2$

$$R_{eq} = \frac{1}{v_{out}/2 - V_{DD}} \int_{V_{DD}}^{v_{out}/2} \frac{V_{DS}(t)}{I_{DS}(t)} dV_{DS}$$

- For the output range we are interested in, the transistor is always in saturation

$$R_{eq} = \frac{-2}{V_{DD}} \int_{V_{DD}}^{v_{out}/2} \frac{V_{DS}}{I_{DSAT}(1 + \lambda V_{DS})} dV_{DS}$$

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Propagation Delay

$$\begin{aligned} R_{eq} &= \frac{-2}{V_{DD}} \int_{V_{DD}}^{v_{out}/2} \frac{V_{DS}}{I_{DSAT}(1 + \lambda V_{DS})} dV_{DS} \\ &= \frac{2}{V_{DD} \lambda^2 I_{SAT}} (\lambda V_{DS} - \ln(1 + \lambda V_{DS})) \Big|_{V_{DD}}^{v_{out}/2} \\ &= \frac{2}{V_{DD} \lambda^2 I_{SAT}} \left(\lambda V_{out} - \left(\lambda V_{DD} - \frac{\lambda^2 V_{DD}^2}{2} + \frac{\lambda^3 V_{DD}^3}{3} - \dots \right) \right) \Big|_{V_{DD}}^{v_{out}/2} \\ &= \frac{2}{V_{DD} I_{SAT}} \left(\frac{V_{out}^2}{2} - \frac{\lambda V_{out}^3}{3} + \dots \right) \Big|_{V_{DD}}^{v_{out}/2} \\ &= \frac{2}{V_{DD} I_{SAT}} \left(\frac{3V_{out}^2}{8} - \frac{7\lambda V_{out}^3}{24} + \dots \right) \end{aligned}$$

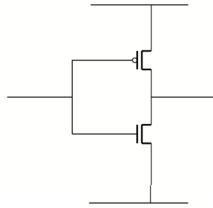
$$= \frac{3}{4} \frac{V_{out}}{I_{SAT}} \left(1 - \frac{7}{9} \lambda V_{out} \right)$$

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Propagation Delay

- Load capacitance**

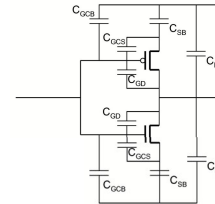


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Propagation Delay

- Load capacitance**
 - Intrinsic capacitance - sum of capacitances at drain - $C_{GD} + C_{DB}$



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Propagation Delay

- Intrinsic capacitance**
 - C_{GD} is composed solely of overlap capacitance
 - The transistors are either in cutoff or in saturation, so no channel capacitance exists
 - The actual load capacitance relative to ground is $2C_{GDO}$ because of Miller effect
 - Miller effect** accounts for an increase in the equivalent input capacitance of an inverting voltage amplifier due to amplification of capacitance between the input and output terminals

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Propagation Delay

$$t_{p,LI} = 0.69 R_{eq} (2C_{GDOin} + 2C_{GDOp} + C_{DBn} + C_{DBp} + C_{ex})$$

- Extrinsic capacitance is composed of wire capacitance and input capacitance of fanout
- Input capacitance is composed of overlap capacitance and channel capacitance
 - Overlap capacitance is $C_{GDO} + C_{GSO}$ (very small)
 - Channel capacitance is C_{oxWL} . Assume worst case

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Propagation Delay

- All capacitances are roughly proportional to W
- Equivalent resistance is inversely proportional to W